

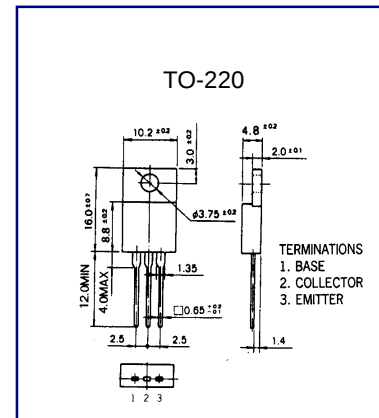


2SD288

NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

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ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	8.0	V
Collector-Emitter Voltage	V_{CE0}	55	V
Emitter-Base voltage	V_{EB0}	5	V
Collector Current (DC)	I_C	3	A
Collector Dissipation ($T_c=25^\circ\text{C}$)	P_C	20	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-50~150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=50\text{V}$, $I_E=0$			50	μA
DC Current Gain	h_{FE1}	$V_{CE}=5\text{V}$, $I_C=0.5\text{A}$	40		240	V
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1\text{A}$, $I_B=0.1\text{A}$			1.0	
Current Gain Bandwidth Product						